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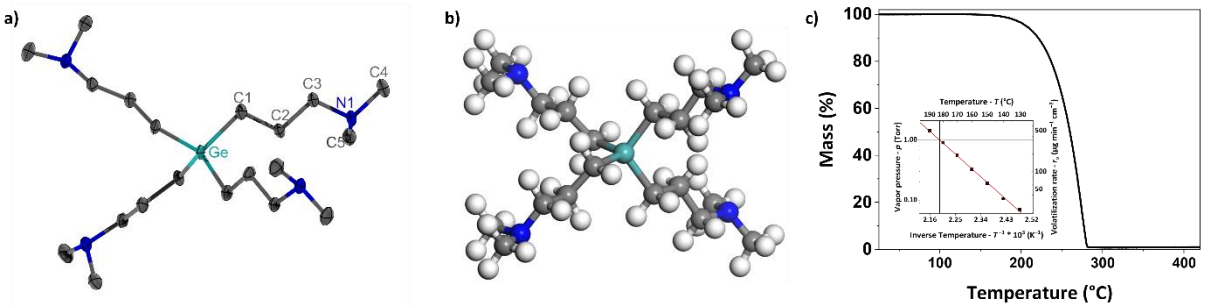

Figure 1. Solid-state structure of $[Ge(DMP)_4]$, as determined by single-crystal XRD (**a**) and DFT calculations (**b**). **c)** Thermogravimetry (TG) curve of $[Ge(DMP)_4]$ with a Clausius-Clapeyron plot for vapor pressure determination shown as an inset.

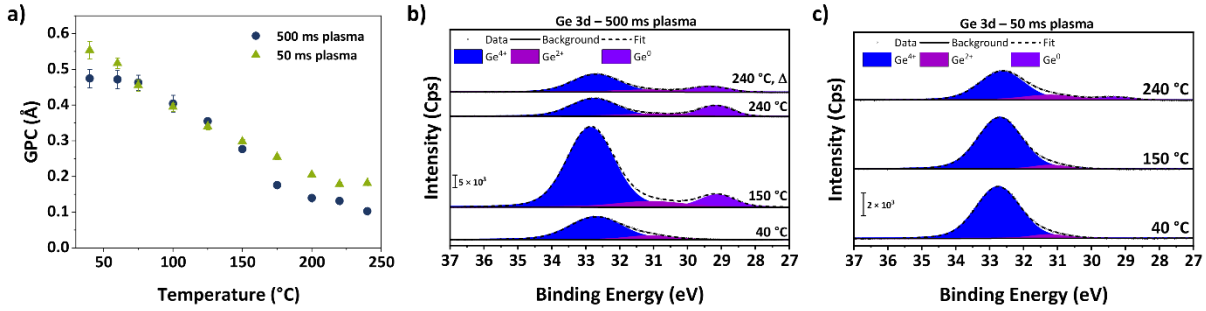

Figure 2. a) Temperature dependency of GeO_x deposited on Si substrates using 500 cycles of a PEALD process with $[Ge(DMP)_4]$ and O_2 plasma pulses of 500 ms (blue circles) and 50 ms (green triangles). XPS Ge 3d core level scans of the resulting thin films with plasma pulse times of **b)** 500 ms and **c)** 50 ms.

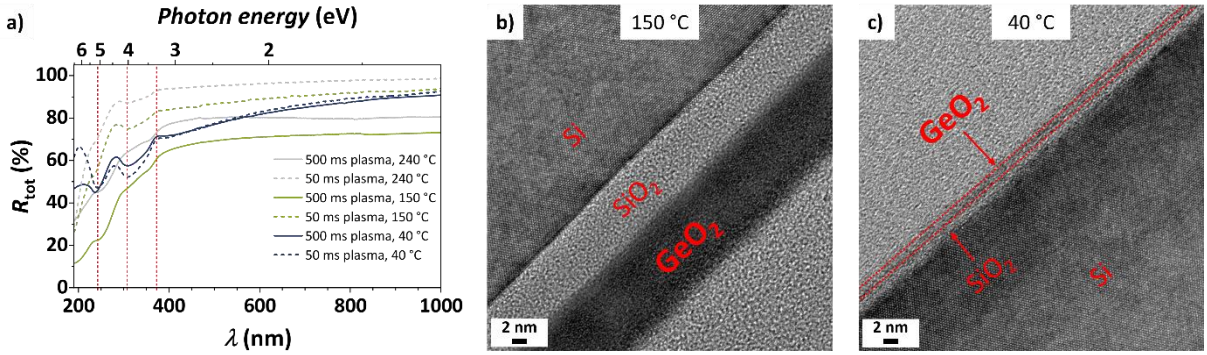

Figure 3. a) UV/Vis spectra of GeO_x thin films deposited using different plasma pulse durations and deposition temperatures. TEM images of GeO_x deposited on Si with native oxide using **b)** 500 PEALD cycles at 150 °C and **c)** eight cycles at 40 °C.